

## Silicon Schottky Barrier Diode

## HSM107S

## ■ Features

- Low  $V_f$  and high efficiency.
- HSM107S which is interconnected in series configuration is designed for protection from not only external excessive voltage but also miss-operation on electric systems.
- MPAK package is suitable for high density surface mounting and high speed assembly.

■ Absolute Maximum Ratings  $T_a = 25^\circ\text{C}$ 

Parameter	Symbol	Value	Unit
Reverse voltage	$V_R$	8	V
Peak forward current	$I_{FM}$	0.1	A
Non-Repetitive Peak forward surge current	$I_{FSM}$ (Note 1)	0.5	A
Average rectified current	$I_o$	50	mA
Junction temperature	$T_j$	125	$^\circ\text{C}$
Storage temperature	$T_{stg}$	-55 to +125	$^\circ\text{C}$

Note

1. Square wave, 10ms

■ Electrical Characteristics  $T_a = 25^\circ\text{C}$ 

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Reverse voltage	$V_R$	$V_R = 1.0 \text{ mA}$	8			pF
Reverse current	$I_R$	$V_R = 5 \text{ V}$			30	$\mu\text{A}$
Forward voltage	$V_F$	$I_F = 10 \text{ mA}$			0.3	V
ESD-Capability (Note 1)		$C=200\text{pF}$ , Both forward and reverse direction 1 pulse.	100			V

Note

1. Failure criterion ;  $I_R \geq 60 \mu\text{A}$  at  $V_R = 5 \text{ V}$

## ■ Marking

Marking	C5
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